AR3311D3H
1-Line Low Capacitance Bi-directional TVS Diode

Description

The AR3311D3H is a 3.3V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR3311D3H has a low capacitance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make AR3311D3H an ideal choice to protect cell phone, wireless systems, and communication equipment.

Features

- 500W peak pulse power (8/20μs)
- Ultra low capacitance: 1pF typical
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±30kV
    - Contact discharge: ±30kV
  - IEC61000-4-5 (Lightning) 30A (8/20μs)
- RoHS Compliant

Mechanical Characteristics

- Package: SOD-323
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

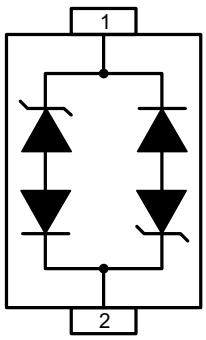
- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

Marking Information

Ordering Information

Part Number	Packaging	Reel Size
AR3311D3H	3000/Tape & Reel	7 inch

Dimensions and Pin Configuration



Circuit and Pin Schematic

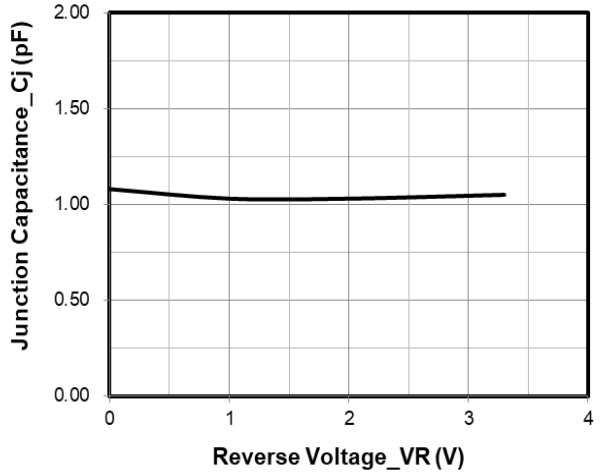
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	500	W
Peak Pulse Current (8/20μs)	I_{PP}	30	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±30 ±30	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

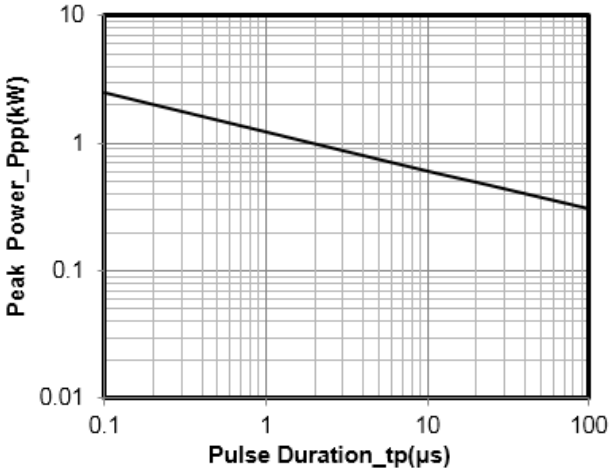
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			3.3	V	
Breakdown Voltage	V_{BR}	3.9			V	I_T = 1mA
Reverse Leakage Current	I_R			0.2	μA	V_{RWM} = 3.3V
Clamping Voltage	V_C			7	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			16	V	I_{PP} = 30A (8 x 20μs pulse)
Junction Capacitance	C_J		1		pF	VR = 0V, f = 1MHz

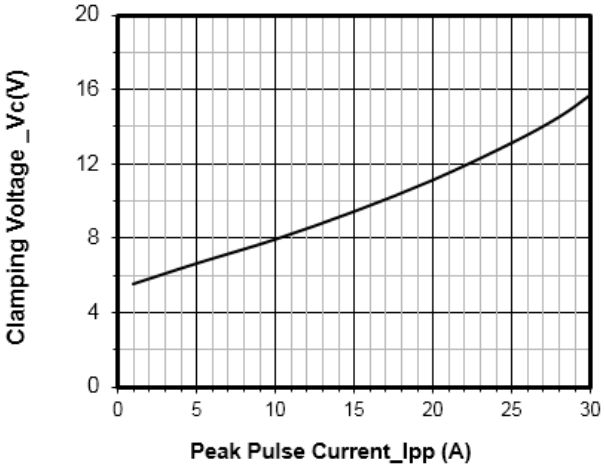
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



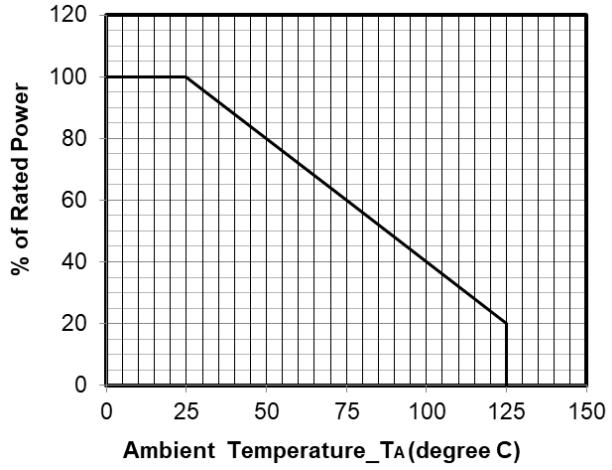
Junction Capacitance vs. Reverse Voltage



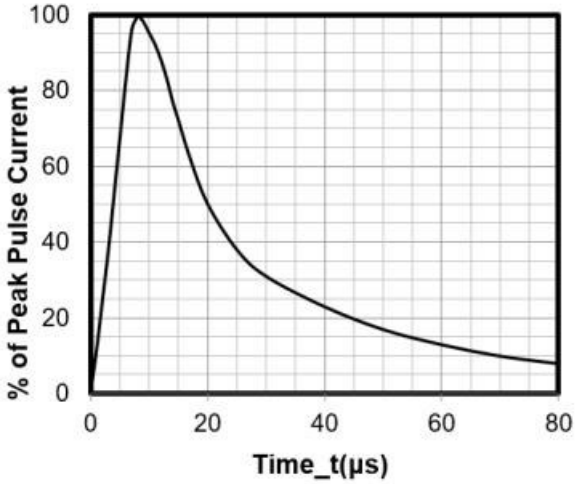
Peak Pulse Power vs. Pulse Time



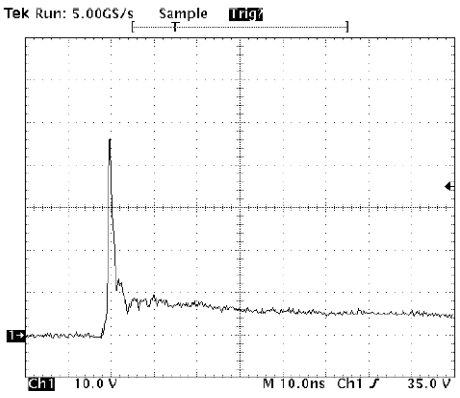
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

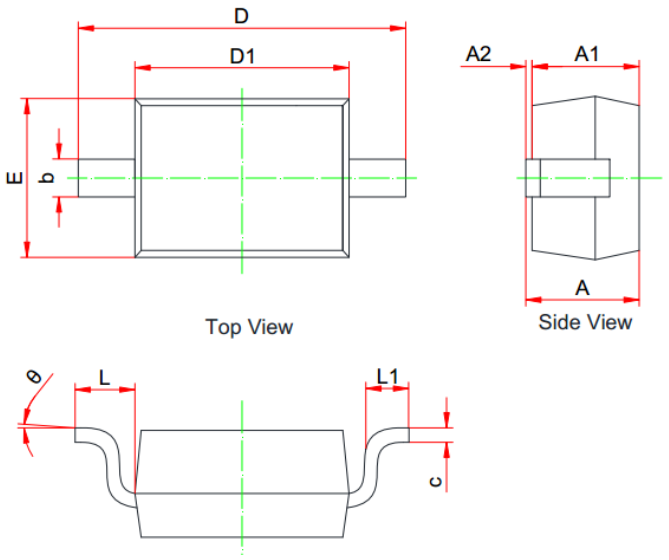


Note：Data is taken with a 10x attenuator

ESD Clamping Voltage

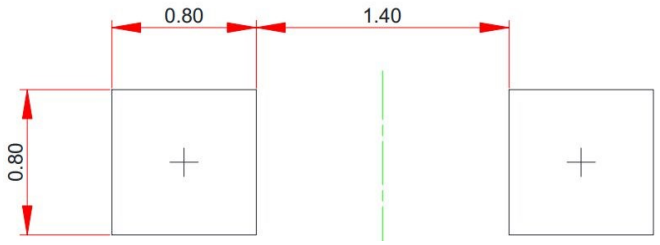
8 kV Contact per IEC61000−4−2

SOD-323 Package Outline Drawing



	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	- -	1.100
A1	0.800	- -	0.900
A2	0.000	- -	0.100
b	0.250	- -	0.400
c	0.080	- -	0.177
D1	1.600	1.700	1.800
D	2.300	- -	2.800
E	1.150	- -	1.400
L	0.475REF		
L1	0.100	- -	0.500
Θ	0°	- -	8°

Suggested Land Pattern



Unit：mm

Contact Information

Applied Power Microelectronics Inc.

Website: http://www.appliedpowermicro.com

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606